

2006 Lester Eastman Conference on High Performance Devices

Poster Session Wednesday August 2, 2006 7:30- 9PM

Duffield / Phillips Atrium

Poster Session Abstracts

[Terahertz sensing of materials](#)

Guangchi Xuan, Suddha Ghosh, Sangcheol Kim, Pengcheng Lv, Takashi Buma, and James K

[CF4 plasma treatment toward GaN transistor applications](#)

Rongming Chu, Chang Soo Suh, Man Hoi Wong, Eric Snow, Nicholas Fichtenbaum, David Brown, Lee McCarthy, Stacia Keller, Feng Wu, James Speck, and Umesh Mishra

[Drift velocity limitation in GaN HEMT channels](#)

Arvydas Matulionis

[High Breakdown Voltage GaN HFETs on Sapphire Substrate](#)

Young Chul Choi, Milan Pophristic, Boris Peres, Michael G. Spencer, and Lester F. Eastman

[Ohmic contact on GaN HEMTs](#)

Yunju Sun and Lester F. Eastman

[Realisation of a Novel GaN/ InN Heterostructure FET Device](#)

D. Alexandrov, R. Perks, K. S.A. Butcher, H. Hirshy, J. Kettle, and M. Wintrebert-Fouquet

[DC characteristics of as-grown AlGaAs/GaAs HBTs and AlGaAs/GaAs/GaN HBTs by direct wafer fusion](#)

Chuanxin Lian, Huili (Grace) Xing, Chad Wang, Lee McCarthy, and Dave Brown

[Photocapacitance of selectively doped AlGaAs/GaAs heterostructures containing deep traps](#)

Nikolai B. Gorev, Inna F. Kodzheshirova, Evgeny N. Privalov, Nina Khuchua, Levan Khvedelidze, and Michael S. Shur

[Low-Loss RF Filter Using MEMS Capacitance Switches](#)

Robert Miles Young

[Temperature-Dependent Microwave Performance of Sb-Heterostructure Backward Diodes for Millimeter-Wave Detection](#)

Ning Su, Ze Zhang, H. P. Moyer, R. D. Rajavel, Joel N. Schulman, and Patrick Fay

[Field and Thermionic-Field Transport at GaAs/AlGaAs/GaAs Heterojunction Barriers](#)

David Vernon Morgan

[Focused thermal beam direct patterning on InGaN during molecular beam epitaxy growth](#)

Xiaodong Chen, William Schaff, and Lester Eastman

[Non-Volatile High speed & Low power Charge Trapping Devices](#)

Moon Kyung Kim, Soo Doo Chae, Chungwoo Kim, and Sandip Tiwari

[A Comparison of N+ type and P+ type Polysilicon Gate in High Speed Non-Volatile Memories](#)

Moon Kyung Kim, Soo Doo Chae, Chungwoo Kim, and Sandip Tiwari

[Accumulated Body MOSFET with Extreme Electrostatic Threshold Voltage Tunability](#)

Ali G. Gokirmak and Sandip Tiwari

[Power Adaptive Control on Dense Configured Super-Self-Aligned Back-Gate Planar Transistors](#)

Hao Lin, Haitao Liu, Arvind Kumar, Uygur Avci, Jay S. Van Delden, Sandip Tiwari, and Arvind Kumar

[Geometry and Short Channel Effects of Enhancement-Mode n-Channel GaN MOSFETs on p and n- GaN/Sapphire Substrates](#)

Weixiao Huang, Tahir Khan, and T. Paul Chow

[Optical Properties of GaInN/GaN Multi-Quantum Well Structure Grown by Metalorganic Vapor Phase Epitaxy](#)

Jayantha Senawiratne, Mingwei zhu, Wei Zhao, Yong Xia, Yufeng Li, Theeradetch Detchprohm, and Christian Wetzel

[4H SiC Betavoltaic Cell For Low Power Applications](#)

MVS Chandrashekhar, Michael Spencer, and Amit Lal

[Self-induced surface texturing of Al₂O₃ by means of Inductively Coupled Plasma Reactive Ion Etching in Cl₂ chemistry](#)

Paolo Batoni, Trushant K. Shah, Dave M. Hodge, Thomas J. Suleski, and Edward B. Stokes

[GaAs-based bipolar cascade lasers with deep quantum well tunnel junctions](#)

Arkadiy Lyakh and Peter Zory

[Extremely high quality AlN grown on \(0001\) sapphire by using metal-organic vapor-phase epitaxy](#)

Kaixuan Chen, Yangang Xi, Frank Mont, Xiaolu Li, Jongkyu Kim, E. Fred Schubert, Wayne Liu, and Joseph Smart

[Spatial Spectral Analysis in High Brightness GaInN/GaN Light Emitting Diodes](#)

Theeradetch Detchprohm, Yong Xia, Jayantha Senawiratne, Yufeng Li, Mingwei Zhu, Wei Zhao, Yangang Xi, E. Fred Schubert, and Christian Wetzel

[Temperature dependence of the quantum efficiency in green GaInN/GaN light emitting diodes](#)

Yufeng Li, Wei Zhao, Yong Xia, Mingwei Zhu, Jayantha Senawiratne, Theeradetch Detchprohm, and Christian Wetzel

[Highly efficient package configurations for white-light-emitting diode lamps](#)

Hong Luo, Jong Kyu Kim, E. Fred Schubert, Jaehee Cho, Cheolsoo Sone, and Yongjo Park

[Electrical Characteristics and Carrier Lifetime Measurements](#)

Peter A. Losee, Ravi J. Kumar, Tat-sing P. Chow, and Ronald J. Gutmann

[SiC MESFET Based MMIC Technology](#)

Mattias Sudow, Kristoffer Andersson, Per-Ake Nilsson, Herbert Zirath, and Niklas Rorsman

[4H-SiC Vertical RESURF Schottky Rectifiers and MOSFETs](#)

Yi Wang, Peter Almern Losee, and T. Paul Chow